



SANYO Semiconductors

# DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

## ATP212 — General-Purpose Switching Device Applications

### Features

- Low ON-resistance.
- Large current.
- Slim package.
- 4V drive.
- Halogen free compliance.

### Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		60	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±20	V
Drain Current (DC)	I <sub>D</sub>		35	A
Drain Current (PW≤10μs)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	105	A
Allowable Power Dissipation	P <sub>D</sub>	T <sub>c</sub> =25°C	40	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	E <sub>AS</sub>		19	mJ
Avalanche Current *2	I <sub>AV</sub>		18	A

Note : \*1 V<sub>DD</sub>=10V, L=100μH, I<sub>AV</sub>=18A

\*2 L≤100μH, Single pulse

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	60			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V			1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μA

Marking : ATP212

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# ATP212

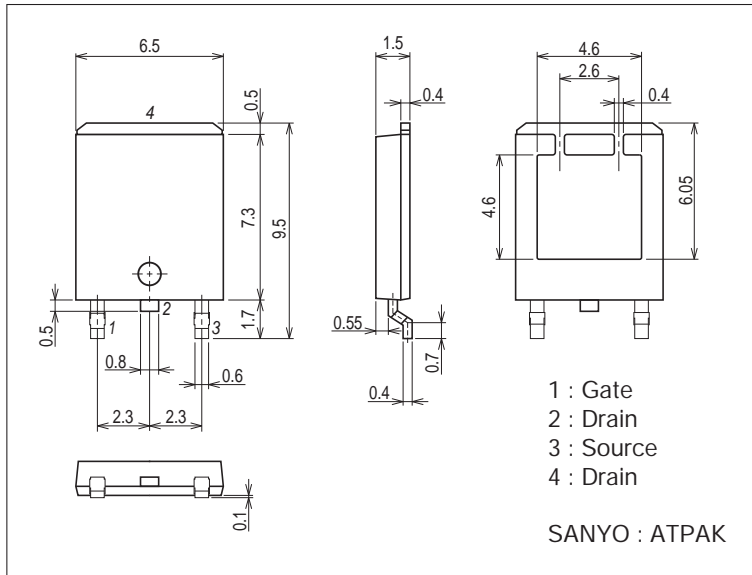
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1mA$	1.2		2.6	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V, I_D=18A$		35		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=18A, V_{GS}=10V$		17	23	m $\Omega$
	$R_{DS(on)2}$	$I_D=9A, V_{GS}=4.5V$		23	33	m $\Omega$
	$R_{DS(on)3}$	$I_D=5A, V_{GS}=4V$		25	37	m $\Omega$
Input Capacitance	$C_{iss}$	$V_{DS}=20V, f=1MHz$		1820		pF
Output Capacitance	$C_{oss}$	$V_{DS}=20V, f=1MHz$		150		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS}=20V, f=1MHz$		100		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		16		ns
Rise Time	$t_r$	See specified Test Circuit.		110		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		125		ns
Fall Time	$t_f$	See specified Test Circuit.		87		ns
Total Gate Charge	$Q_g$	$V_{DS}=30V, V_{GS}=10V, I_D=35A$		34.5		nC
Gate-to-Source Charge	$Q_{gs}$	$V_{DS}=30V, V_{GS}=10V, I_D=35A$		6.5		nC
Gate-to-Drain "Miller" Charge	$Q_{gd}$	$V_{DS}=30V, V_{GS}=10V, I_D=35A$		6.8		nC
Diode Forward Voltage	$V_{SD}$	$I_S=35A, V_{GS}=0V$		0.96	1.2	V

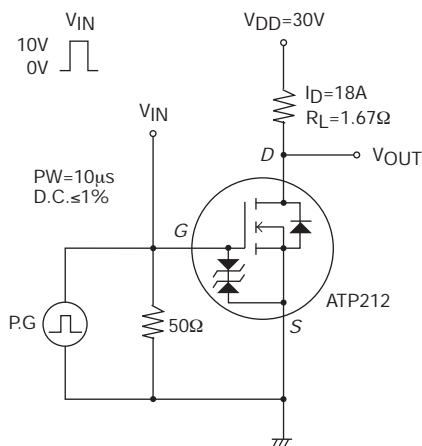
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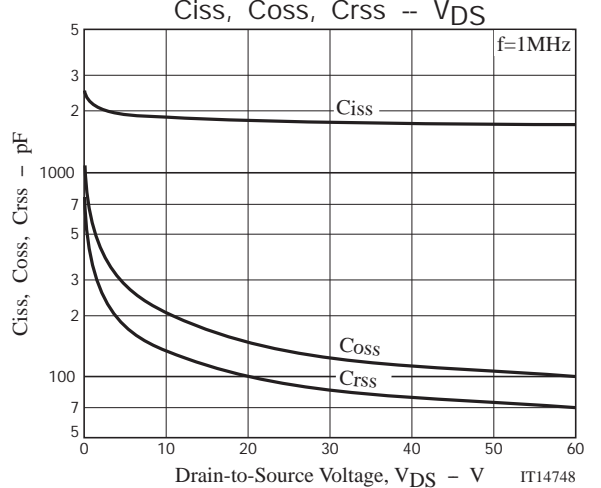
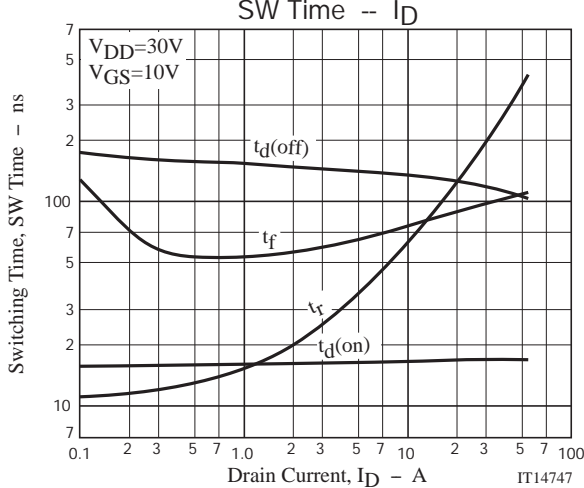
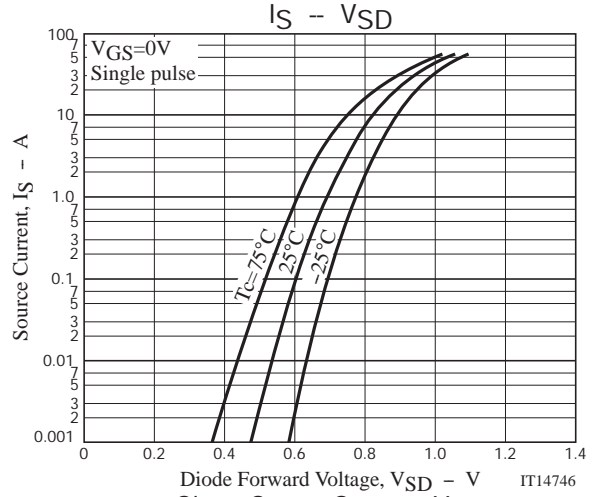
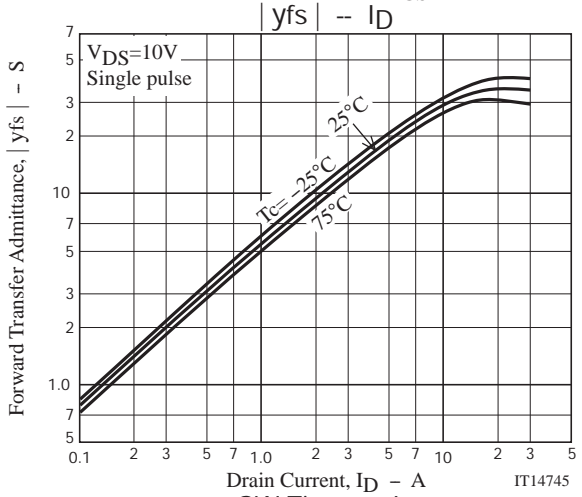
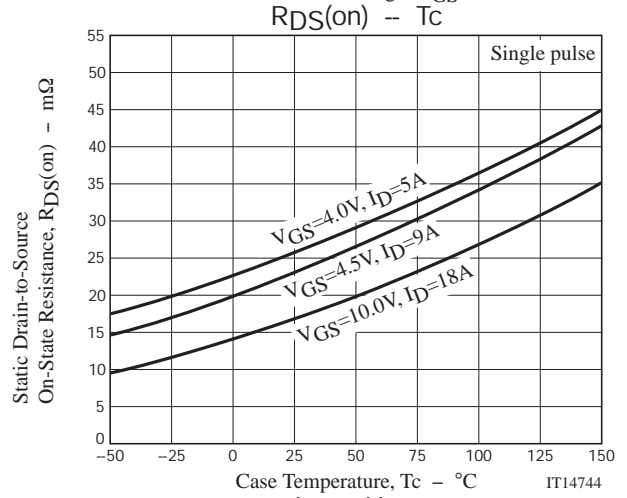
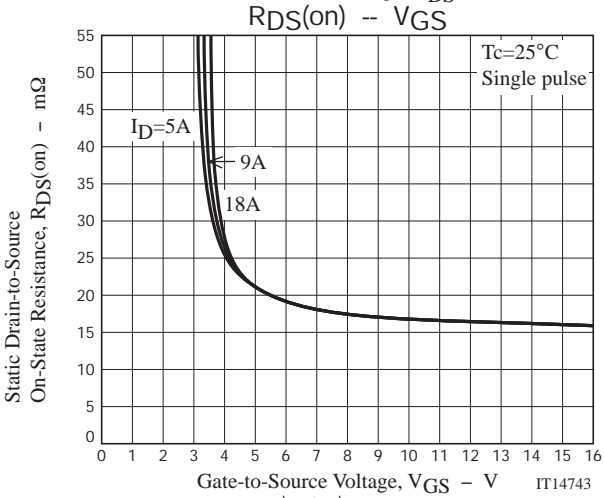
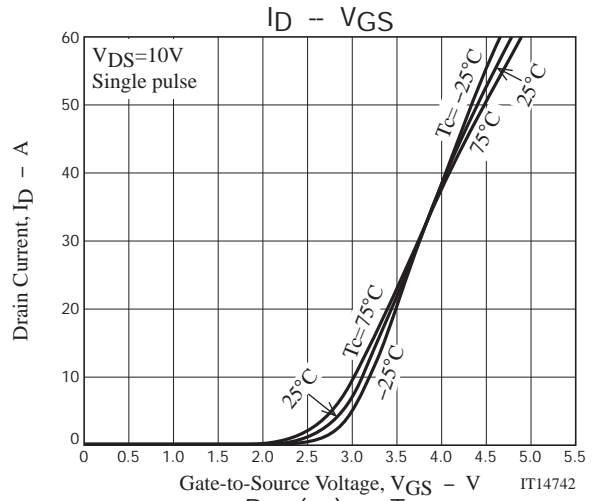
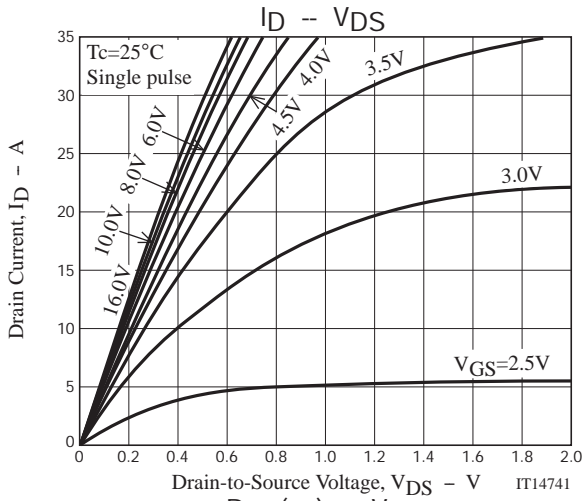
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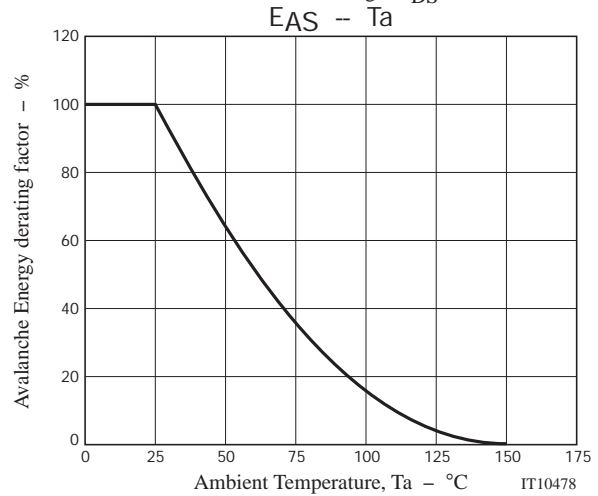
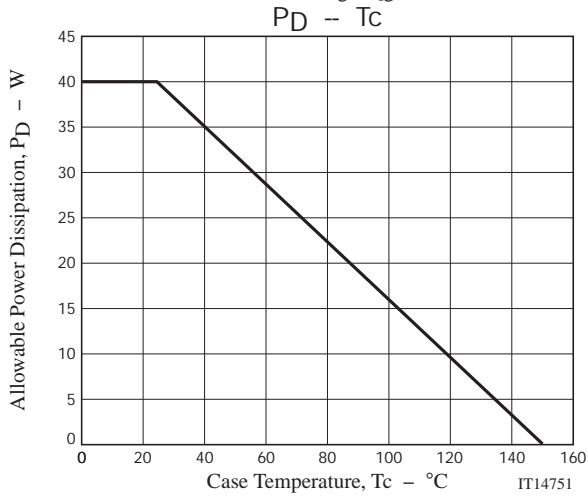
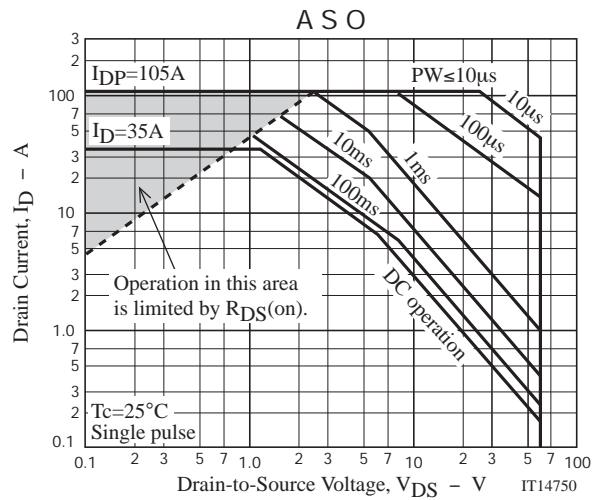
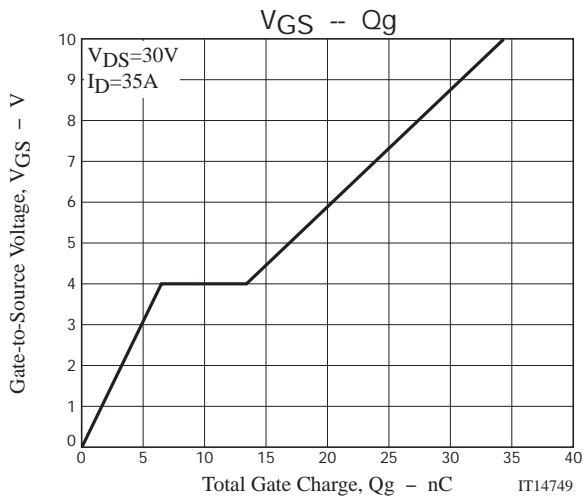
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## Switching Time Test Circuit







Note on usage : Since the ATP212 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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